20 V, single P-channel Trench MOSFET 5 September 2012

Product data sheet

1. Product profile

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1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Trench MOSFET technology
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- Exposed drain pad for excellent thermal conduction
- Tin-plated 100 % solderable side pads for optical solder inspection

1.3 Applications

. .

- Charging switch for portable devices
- DC-to-DC converters
- Power management in battery-driven portable devices
- Hard disk and computing power management

1.4 Quick reference data

| Table 1. Qui | ck reference data | | | | | | |
|------------------------|----------------------------------|--|-----|-----|-----|------|------|
| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
| V _{DS} | drain-source voltage | T _j = 25 °C | | - | - | -20 | V |
| V _{GS} | gate-source voltage | | | -12 | - | 12 | V |
| I _D | drain current | V _{GS} = -4.5 V; T _{amb} = 25 °C; t ≤ 5 s | [1] | - | - | -7.9 | А |
| Static characteristics | | | | | | | |
| R _{DSon} | drain-source on-state resistance | V_{GS} = -4.5 V; I _D = -5.5 A; T _j = 25 °C | | - | 30 | 37 | mΩ |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².





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2. Pinning information

| Table 2. | Pinning | information | | |
|----------|---------|-------------|-----------------------|----------------|
| Pin | Symbol | Description | Simplified outline | Graphic symbol |
| 1 | D | drain | | D |
| 2 | D | drain | | |
| 3 | G | gate | | G |
| 4 | S | source | | S 017aaa257 |
| 5 | D | drain | Transparent top view | |
| 6 | D | drain | DFN2020MD-6 (SOT1220) | |
| 7 | D | drain | | |
| 8 | S | source | | |

3. Ordering information

| Table 3. Ordering information | | | | | |
|-------------------------------|-------------|--|---------|--|--|
| Type number | Package | | | | |
| | Name | Description | Version | | |
| PMPB33XP | DFN2020MD-6 | plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals | SOT1220 | | |

4. Marking

| Table 4. Marking codes | |
|------------------------|--------------|
| Type number | Marking code |
| PMPB33XP | 1S |

5. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

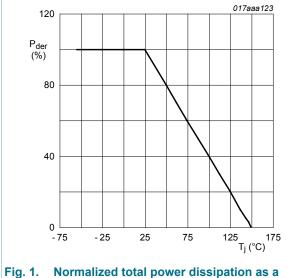
| Symbol | Parameter | Conditions | | Min | Мах | Unit |
|------------------|-------------------------|---|-----|-----|-----------------|-----------------|
| V _{DS} | drain-source voltage | T _j = 25 °C | | - | -20 | V |
| V _{GS} | gate-source voltage | | | -12 | 12 | V |
| I _D | drain current | V _{GS} = -4.5 V; T _{amb} = 25 °C; t ≤ 5 s | [1] | - | -7.9 | А |
| | | V _{GS} = -4.5 V; T _{amb} = 25 °C | [1] | - | -5.5 | А |
| | | V _{GS} = -4.5 V; T _{amb} = 100 °C | [1] | - | -3.5 | А |
| I _{DM} | peak drain current | T_{amb} = 25 °C; single pulse; $t_p \le 10 \ \mu s$ | | - | -22 | А |
| P _{tot} | total power dissipation | T _{amb} = 25 °C | [1] | - | 1.7 | W |
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| Symbol | Parameter | Conditions | | Min | Max | Unit |
|--------------------|----------------------|-----------------------------------|-----|-----|------|------|
| | | T _{amb} = 25 °C; t ≤ 5 s | [1] | - | 3.5 | W |
| | | T _{sp} = 25 °C | | - | 12.5 | W |
| Tj | junction temperature | | | -55 | 150 | °C |
| T _{amb} | ambient temperature | | | -55 | 150 | °C |
| T _{stg} | storage temperature | | | -65 | 150 | °C |
| Source-drain diode | | | | | | |
| I _S | source current | T _{amb} = 25 °C | [1] | - | -1.9 | А |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

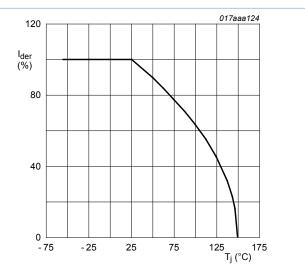
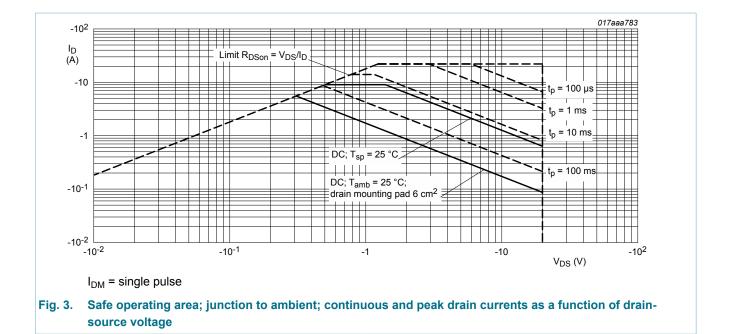


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

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6. Thermal characteristics

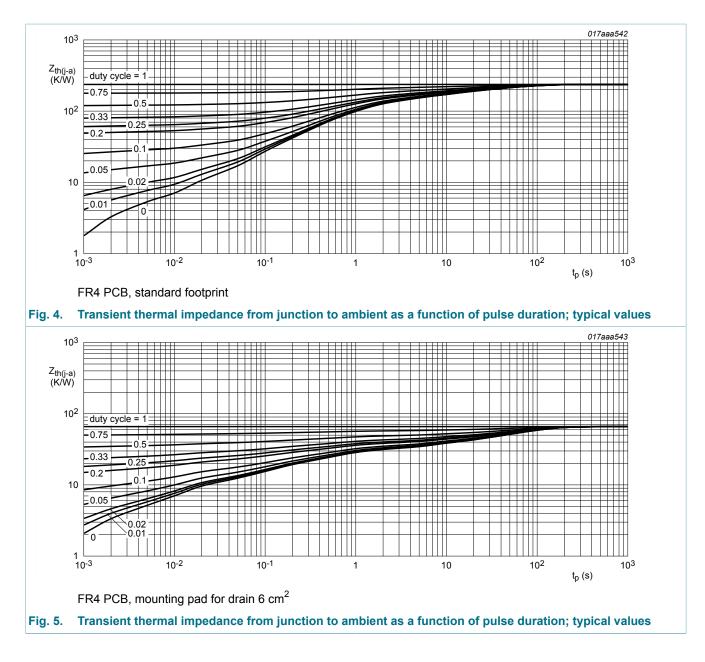
| Table 6. T | Thermal characteristics | | | | | | |
|-----------------------|--|----------------------|-----|-----|-----|-----|------|
| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
| R _{th(j-a)} | thermal resistance | in free air | [1] | - | 235 | 270 | K/W |
| | from junction to ambient | | [2] | - | 67 | 74 | K/W |
| | ambient | in free air; t ≤ 5 s | [2] | - | 33 | 36 | K/W |
| R _{th(j-sp)} | thermal resistance from junction to solder point | | | - | 5 | 10 | K/W |

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

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7. Characteristics

| Table 7. C | haracteristics | | | | | | | |
|------------------------|-----------------------------------|--|--|-------|-------|----------------|-------------------|--|
| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit | |
| Static characteristics | | | | | | | | |
| V _{(BR)DSS} | drain-source breakdown voltage | I_D = -250 µA; V_{GS} = 0 V; T_j = 25 °C | | -20 | - | - | V | |
| V _{GSth} | gate-source threshold voltage | I_D = -250 µA; V_{DS} = V_{GS} ; T_j = 25 °C | | -0.47 | -0.68 | -0.9 | V | |
| I _{DSS} | drain leakage current | V_{DS} = -20 V; V_{GS} = 0 V; T_j = 25 °C | | - | - | -1 | μA | |
| I _{GSS} | gate leakage current | V_{GS} = -12 V; V_{DS} = 0 V; T_j = 25 °C | | - | - | -100 | nA | |
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| Symbol | Parameter | Conditions | Min | Тур | Мах | Unit |
|---------------------|------------------------------|--|-----|------|-----|------|
| | | V _{GS} = 12 V; V _{DS} = 0 V; T _j = 25 °C | - | - | 100 | nA |
| R _{DSon} | drain-source on-state | V_{GS} = -4.5 V; I _D = -5.5 A; T _j = 25 °C | - | 30 | 37 | mΩ |
| | resistance | V _{GS} = -4.5 V; I _D = -5.5 A; T _j = 150 °C | - | 45 | 56 | mΩ |
| | | V _{GS} = -2.5 V; I _D = -5 A; T _j = 25 °C | - | 35 | 46 | mΩ |
| | | V _{GS} = -1.8 V; I _D = -2.1 A; T _j = 25 °C | - | 45 | 65 | mΩ |
| 9 _{fs} | forward transconductance | V _{DS} = -10 V; I _D = -5.5 A; T _j = 25 °C | - | 28 | - | S |
| R _G | gate resistance | f = 1 MHz | - | 4.5 | - | Ω |
| Dynamic cl | haracteristics | · · · | | I | 1 | |
| Q _{G(tot)} | total gate charge | V_{DS} = -10 V; I _D = -5.5 A; V _{GS} = -4.5 V; | - | 15 | 23 | nC |
| Q _{GS} | gate-source charge | T _j = 25 °C | - | 2 | - | nC |
| Q _{GD} | gate-drain charge | | - | 4 | - | nC |
| C _{iss} | input capacitance | V _{DS} = -10 V; f = 1 MHz; V _{GS} = 0 V; | - | 1575 | - | pF |
| C _{oss} | output capacitance | T _j = 25 °C | - | 145 | - | pF |
| C _{rss} | reverse transfer capacitance | | - | 125 | - | pF |
| t _{d(on)} | turn-on delay time | V_{DS} = -10 V; I _D = -5.5 A; V _{GS} = -4.5 V; | - | 12 | - | ns |
| t _r | rise time | $R_{G(ext)} = 6 \Omega; T_j = 25 °C$ | - | 42 | - | ns |
| t _{d(off)} | turn-off delay time | | - | 62 | - | ns |
| t _f | fall time | | - | 23 | - | ns |

Source-drain diode

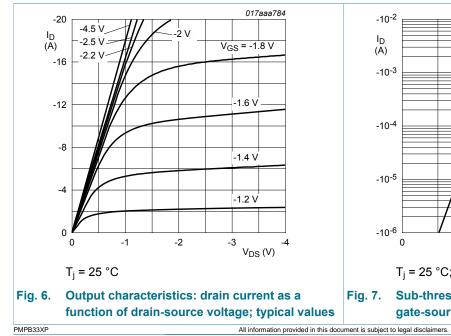
 V_{SD}

 I_{S} = -1.9 A; V_{GS} = 0 V; T_{j} = 25 °C

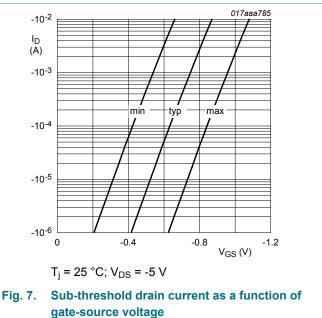
-1.2

V

-0.6



source-drain voltage

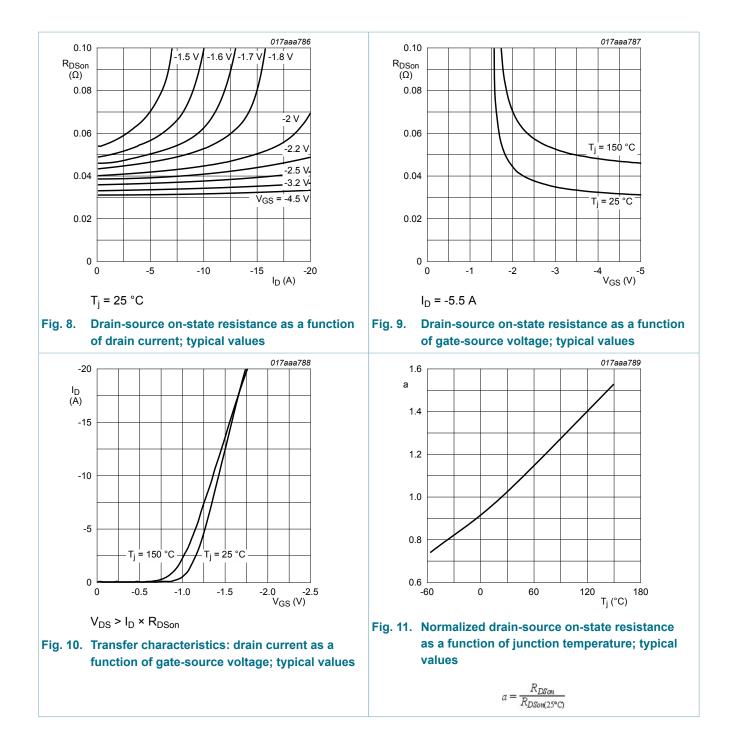


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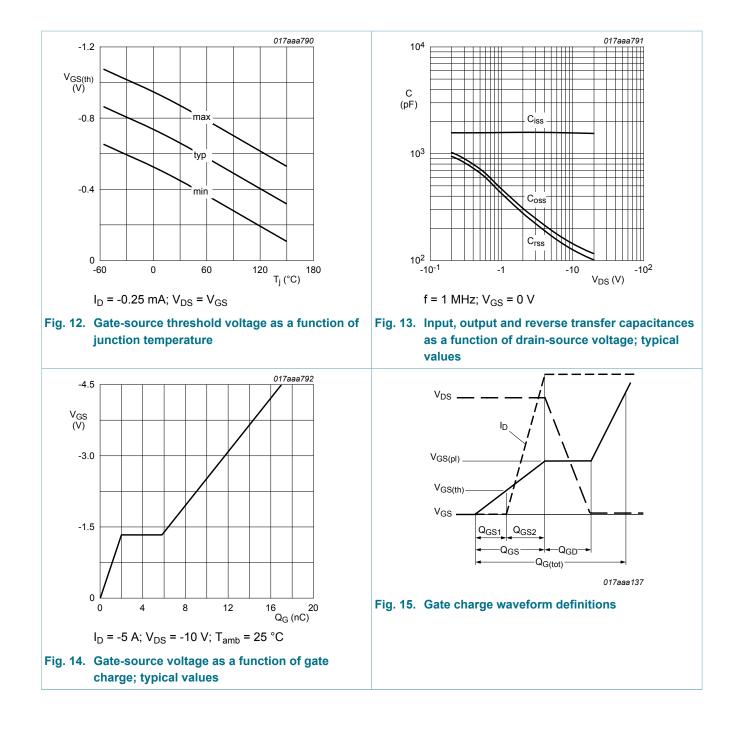
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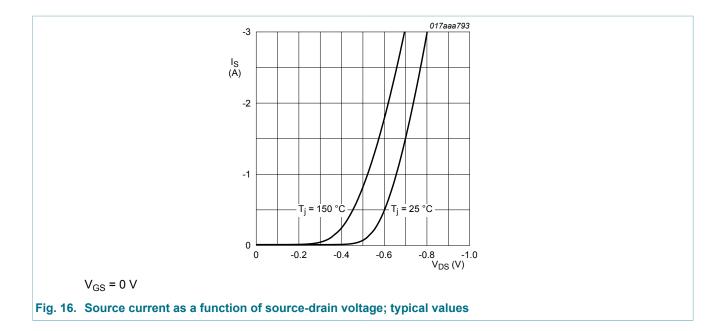
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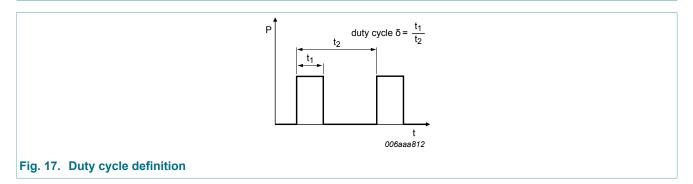


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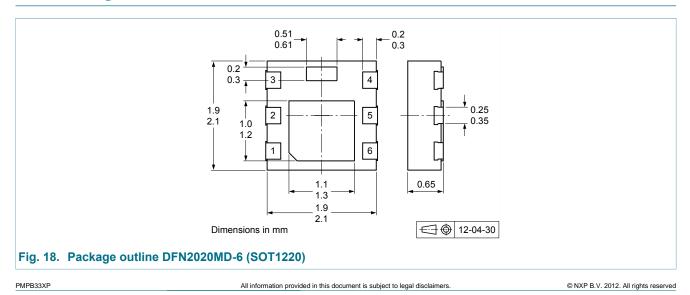
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8. Test information

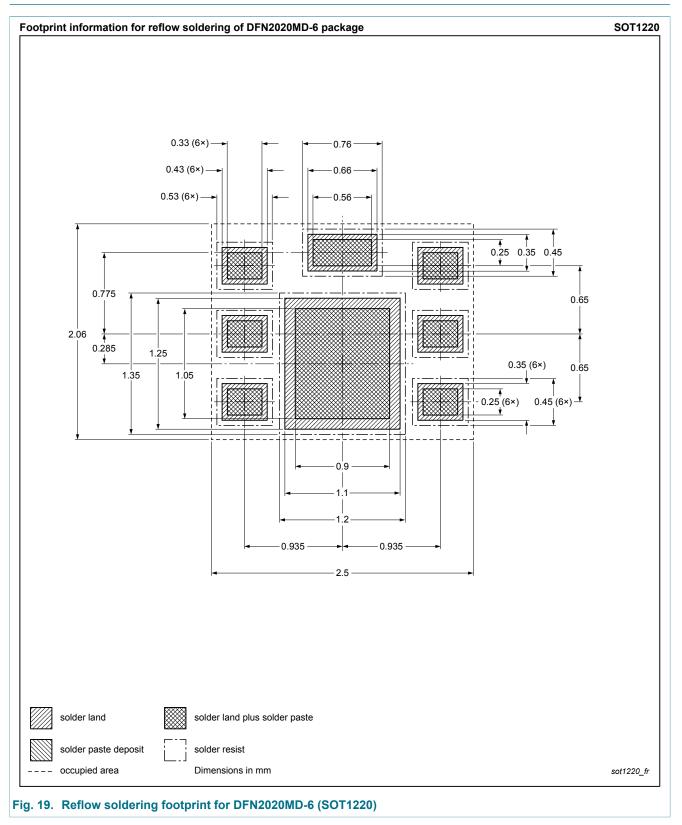


9. Package outline



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10. Soldering



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11. Revision history

| Table 8. Revision history | | | | | |
|---------------------------|--------------|--------------------|---------------|------------|--|
| Data sheet ID | Release date | Data sheet status | Change notice | Supersedes | |
| PMPB33XP v.1 | 20120905 | Product data sheet | - | - | |

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12. Legal information

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|--------------------------------------|-------------------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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